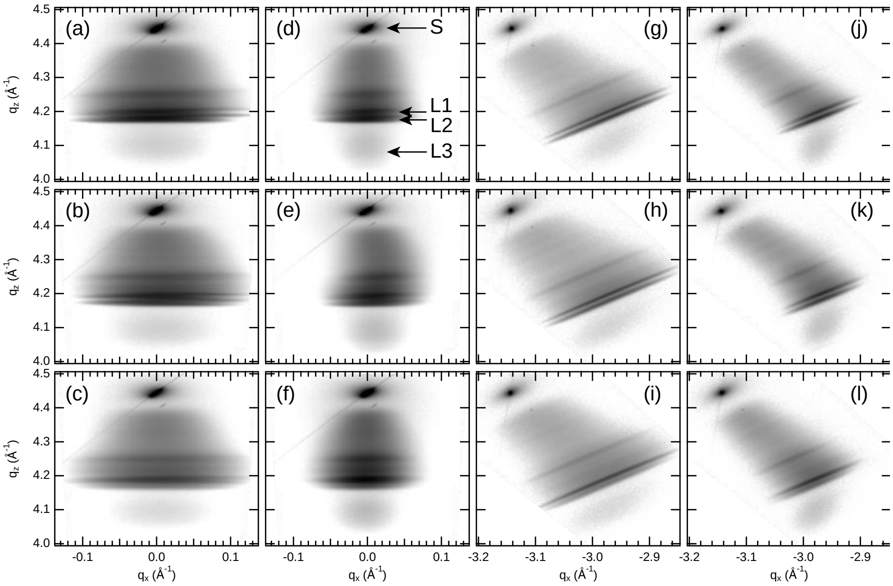

Fig. 1: X ray diffraction reciprocal space maps of (004) (a-f) and (224) reflections (g-l) of InAs QWs along the [110] direction (a-c, g-i) and along the [-110] direction (d-f, j-l) with t = 300 nm (a,d,g,j) , 150 nm, (b,e,h,k) and 50 nm (c,f,i,l).

Substrate, $In_{0.81}Al_{0.19}As$, $In_{0.84}Al_{0.16}As$, and InAs peaks are labelled as S, L1, L2 and L3, respectively.

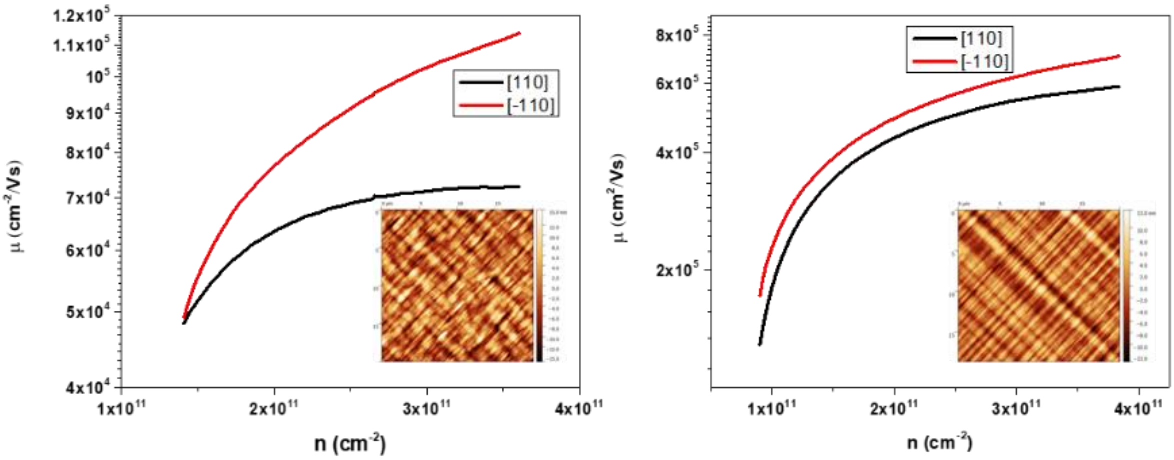

Fig. 2: Mobility vs. charge density along [110] and [-110] for t = 50nm (left) and 300nm (right). Inset: corresponding AFM images of top surfaces.